2N6057 thru 2N6059 (See 2N6050)

Complementary Silicon Plastic Power Transistors

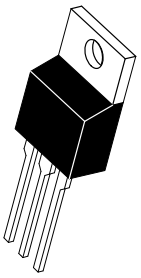
PNP
2N6107
2N6109*
2N6111
NPN
2N6288
2N6292*

*Motorola Preferred Device

. . . designed for use in general–purpose amplifier and switching applications.

- DC Current Gain Specified to 7.0 Amperes
  h_{FE} = 30–150 @ I_C = 3.0 Adc — 2N6111, 2N6288
  = 2.3 (Min) @ I_C = 7.0 Adc — All Devices
- Collector–Emitter Sustaining Voltage —
  $V_{CEO(sus)}$ = 30 Vdc (Min) — 2N6111, 2N6288
  = 50 Vdc (Min) — 2N6109
  = 70 Vdc (Min) — 2N6107, 2N6292
- High Current Gain — Bandwidth Product
  f_T = 4.0 MHz (Min) @ I_C = 500 mAdc — 2N6288, 90, 92
  = 10 MHz (Min) @ I_C = 500 mAdc — 2N6107, 09, 11
- TO–220AB Compact Package

7 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 30–50–70 VOLTS 40 WATTS



CASE 221A–06 TO–220AB

***MAXIMUM RATINGS**

Rating	Symbol	2N6111 2N6288	2N6109	2N6107 2N6292	Unit
Collector–Emitter Voltage	V_{CEO}	30	50	70	Vdc
Collector–Base Voltage	V_{CB}	40	60	80	Vdc
Emitter–Base Voltage	V_{EB}	5.0			Vdc
Collector Current — Continuous Peak	I_C	7.0 10			Adc
Base Current	I_B	3.0			Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	40 0.32			Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.125	°C/W

* Indicates JEDEC Registered Data.

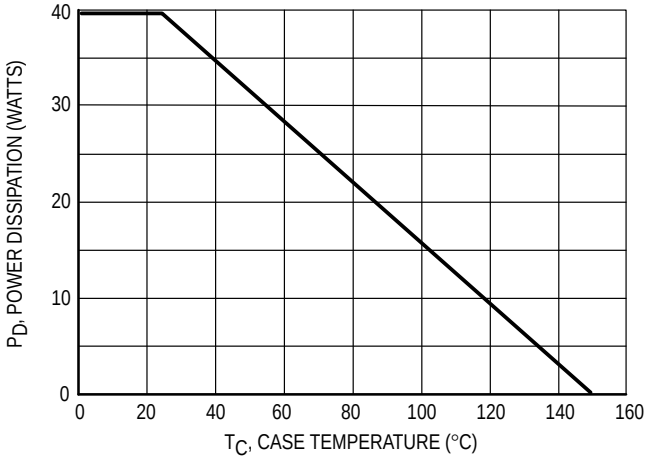


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 2

***ELECTRICAL CHARACTERISTICS** (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1)		$V_{CEO(sus)}$			Vdc
(I_C = 100 mAdc, I_B = 0)	2N6111, 2N6288		30	—	
	2N6109		50	—	
	2N6107, 2N6292		70	—	
Collector Cutoff Current		I_{CEO}			mAdc
(V_{CE} = 20 Vdc, I_B = 0)	2N6111, 2N6288		—	1.0	
(V_{CE} = 40 Vdc, I_B = 0)	2N6109		—	1.0	
(V_{CE} = 60 Vdc, I_B = 0)	2N6107, 2N6292		—	1.0	
Collector Cutoff Current		I_{CEX}			μAdc
(V_{CE} = 40 Vdc, $V_{EB(off)}$ = 1.5 Vdc)	2N6111, 2N6288		—	100	
(V_{CE} = 60 Vdc, $V_{EB(off)}$ = 1.5 Vdc)	2N6109		—	100	
(V_{CE} = 80 Vdc, $V_{EB(off)}$ = 1.5 Vdc)	2N6107, 2N6292		—	100	
(V_{CE} = 30 Vdc, $V_{EB(off)}$ = 1.5 Vdc, T_C = 150°C)	2N6111, 2N6288		—	2.0	mAdc
(V_{CE} = 50 Vdc, $V_{EB(off)}$ = 1.5 Vdc, T_C = 150°C)	2N6109		—	2.0	
(V_{CE} = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc, T_C = 150°C)	2N6107, 2N6292		—	2.0	
Emitter Cutoff Current		I_{EBO}	—	1.0	mAdc
(V_{BE} = 5.0 Vdc, I_C = 0)					
ON CHARACTERISTICS (1)					
DC Current Gain		h_{FE}			—
(I_C = 2.0 Adc, V_{CE} = 4.0 Vdc)	2N6107, 2N6292		30	150	
(I_C = 2.5 Adc, V_{CE} = 4.0 Vdc)	2N6109		30	150	
(I_C = 3.0 Adc, V_{CE} = 4.0 Vdc)	2N6111, 2N6288		30	150	
(I_C = 7.0 Adc, V_{CE} = 4.0 Vdc)	All Devices		2.3	—	
Collector–Emitter Saturation Voltage		$V_{CE(sat)}$	—	3.5	Vdc
(I_C = 7.0 Adc, I_B = 3.0 Adc)					
Base–Emitter On Voltage		$V_{BE(on)}$	—	3.0	Vdc
(I_C = 7.0 Adc, V_{CE} = 4.0 Vdc)					
DYNAMIC CHARACTERISTICS					
Current Gain — Bandwidth Product (2)		f_T			MHz
(I_C = 500 mAdc, V_{CE} = 4.0 Vdc, f_{test} = 1.0 MHz)	2N6288, 92		4.0	—	
	2N6107, 09, 11		10	—	
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{ob}	—	250	pF
Small–Signal Current Gain (I_C = 0.5 Adc, V_{CE} = 4.0 Vdc, f = 50 kHz)		h_{fe}	20	—	—

* Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

(2) $f_T = |h_{fe}| \bullet f_{test}$.

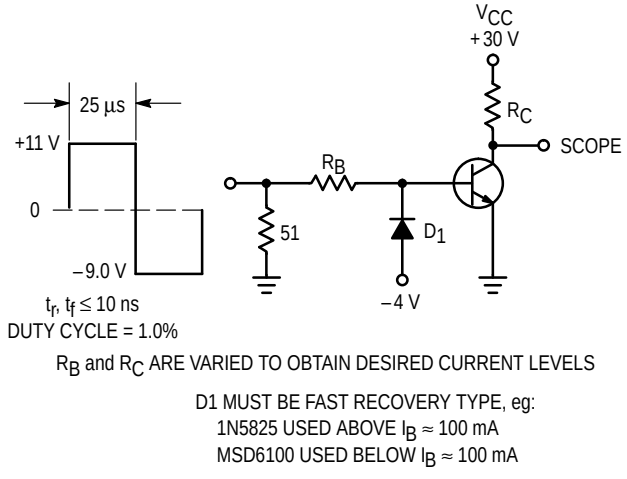


Figure 2. Switching Time Test Circuit

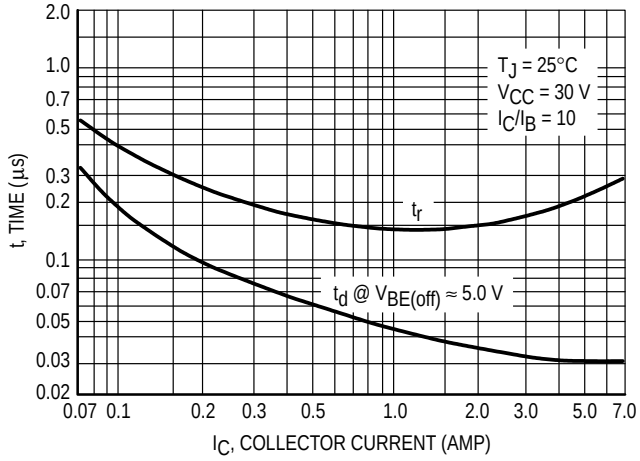


Figure 3. Turn–On Time

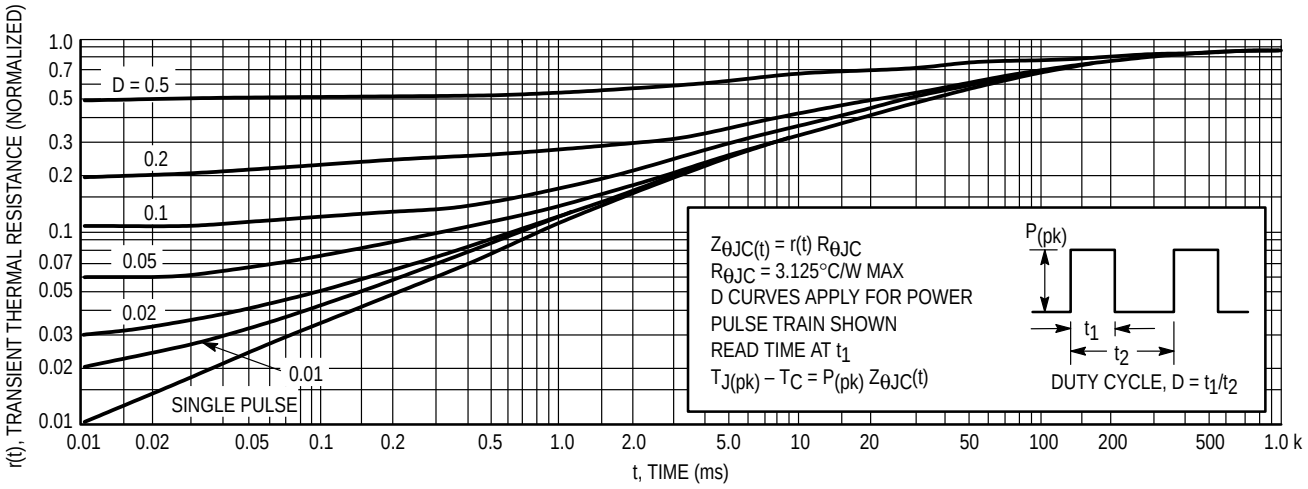


Figure 4. Thermal Response

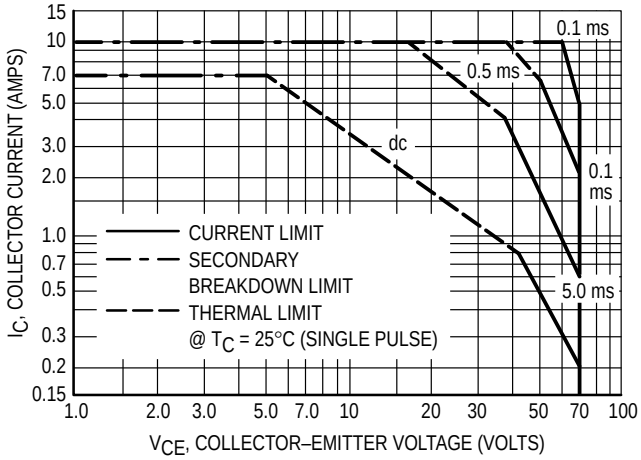


Figure 5. Active–Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq$ 150°C. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

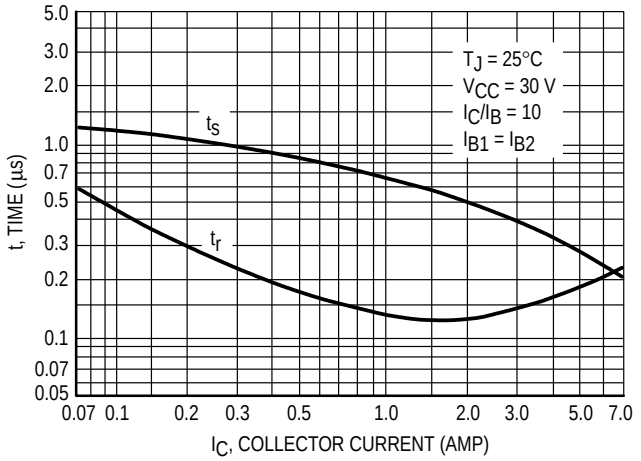


Figure 6. Turn–Off Time

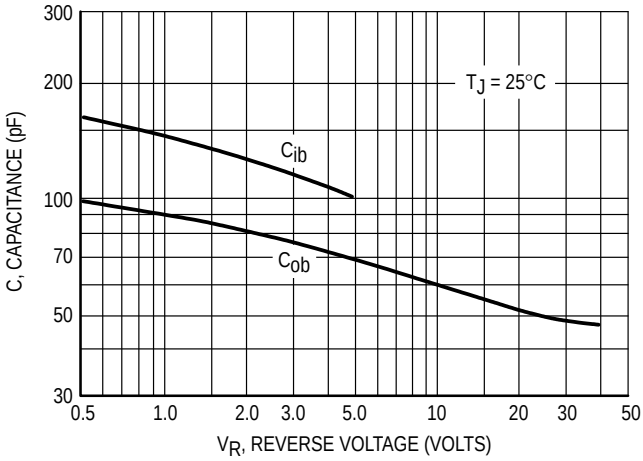
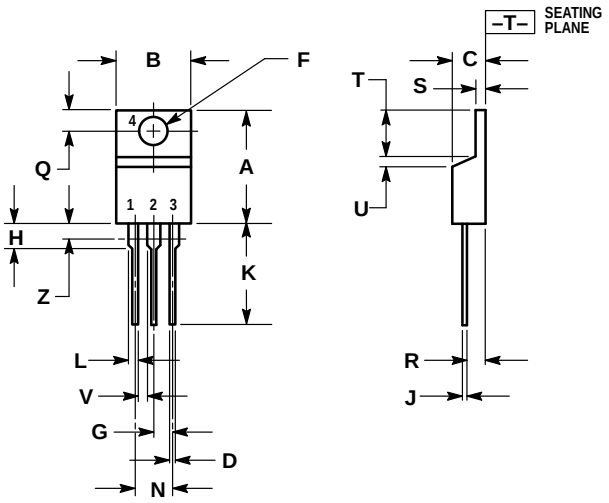


Figure 7. Capacitance

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

CASE 221A–06
TO–220AB
ISSUE Y

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